

APPENDIX TO AMENDMENT

FILED OCTOBER 18, 2002

Amended claim:

1. (Twice amended) A semiconductor device comprising:
a Cu film provided above a main surface of a semiconductor substrate and used as a wiring;
an intermediate layer formed at least on the Cu film, the intermediate layer comprising a TaN film formed on the Cu film and a Ta film formed on the TaN film, wherein a thickness of the TaN film is 20 nm or more; and
an Al film formed on the Ta film and used as a pad.
15. (Twice amended) The semiconductor device according to claim 1 [13], wherein a thickness of the TaN film is 40 nm or more.
16. (Amended) A semiconductor device comprising:
a Cu film provided above a main surface of a semiconductor substrate and used as a wiring;
an intermediate layer formed at least on the Cu film, the intermediate layer comprising a TaN film formed on the Cu film and a Ta film formed on the TaN film; [, and]
an Al film formed on the Ta film and used as a pad, the Al film having an extending portion under which the Cu film is not formed; and

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a conductive connection member connected to the Al film at the extending portion.

21. (Twice amended) The semiconductor device according to claim 16 [20], wherein a thickness of the TaN film is 20 nm or more.

22. (Twice amended) The semiconductor device according to claim 16 [20], wherein a thickness of the TaN film is 40 nm or more.

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